2SD1470

Silicon NPN Epitaxial, Darlington

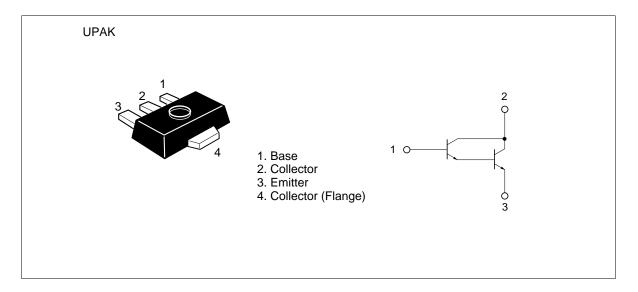
HITACHI

ADE-208-1153 (Z) 1st. Edition Mar. 2001

Application

Low frequency power amplifier

Outline





2SD1470

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	60	V
Emitter to base voltage	V _{EBO}	7	V
Collector current	I _c	1	Α
Collector peak current	i _{C(peak)} *1	2	А
Collector power dissipation	P _C *2	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW ≤ 10 ms, Duty cycle ≤ 20%

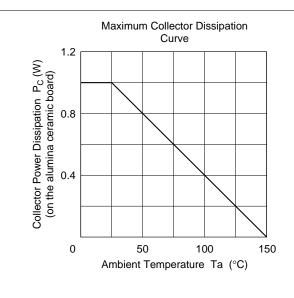
2. Value on the alumina ceramic board (12.5 x 30 x 0.7 mm)

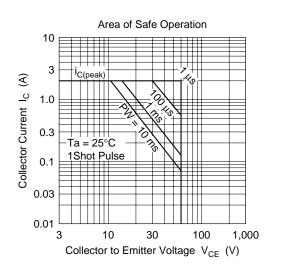
Electrical Characteristics ($Ta = 25^{\circ}C$)

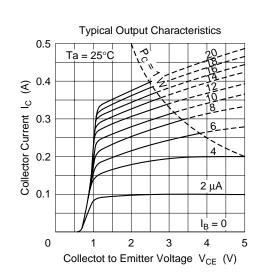
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	60	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	60	_	_	V	I_{C} = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	10	μΑ	$V_{CB} = 60 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	10	μΑ	$V_{EB} = 7 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE}	2000	_	10000)	$V_{CE} = 3 \text{ V}, I_{C} = 0.5 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1.5	V	$I_{\rm C}$ = 500 mA, $I_{\rm B}$ = 0.5 mA* ¹
Base to emitter saturation voltage	$V_{BE(sat)}$	_	_	2.0	V	$I_{\rm C}$ = 500 mA, $I_{\rm B}$ = 0.5 mA* ¹

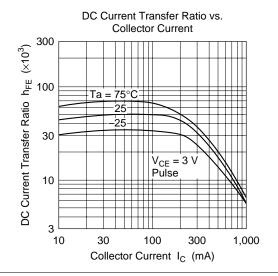
Notes: 1. Pulse test

2. Marking is "AT".

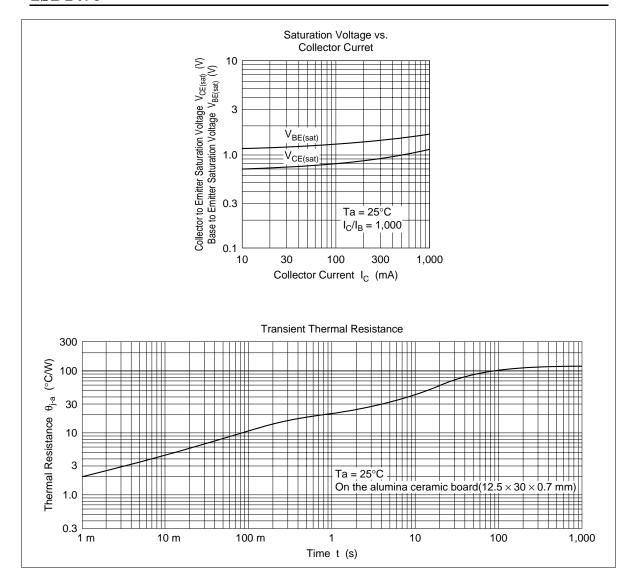




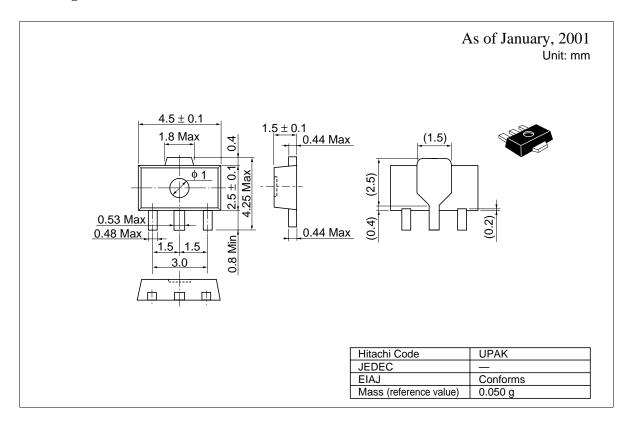




2SD1470



Package Dimensions



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